

### FEATURES

- **OEC™** Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference
- **Bidirectional Interface Between GTLP Signal** Levels and LVTTL Logic Levels
- GTLP-to-LVTTL 1-to-6 Fanout Driver
- LVTTL-to-GTLP 1-to-2 Fanout Driver
- LVTTL Interfaces Are 5-V Tolerant
- Medium-Drive GTLP Outputs (50 mA)
- **Reduced-Drive LVTTL Outputs** (-12 mA/12 mA)
- Variable Edge-Rate Control (ERC) Input Selects GTLP Rise and Fall Times for Optimal Data-Transfer Rate and Signal Integrity in **Distributed Loads**
- Ioff and Power-Up 3-State Support Hot . Insertion
- Distributed V<sub>cc</sub> and GND Pins Minimize **High-Speed Switching Noise**
- Latch-Up Performance Exceeds 100 mA Per JESD 78. Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

## **DESCRIPTION/ORDERING INFORMATION**

The SN74GTLP817 is a medium-drive fanout driver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard TTL or LVTTL) backplane operation is a direct result of GTLP reduced output swing (<1 V), reduced input threshold levels, improved differential input, and OEC<sup>™</sup> circuitry. The improved GTLP OEC circuitry minimizes bus settling time and has been designed and tested using several backplane models. The medium drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 19  $\Omega$ . BO1 and BO2 can be tied together to drive an equivalent load impedance down to 11  $\Omega$ .

GTLP is the Texas Instruments (TI™) derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLP817 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL ( $V_{TT}$  = 1.2 V and  $V_{RFF}$  = 0.8 V) or GTLP  $(V_{TT} = 1.5 \text{ V and } V_{REF} = 1 \text{ V})$  signal levels.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs. V<sub>RFF</sub> is the B-port differential input reference voltage.

GNDT is the TTL output ground, while GNDG is the GTLP output ground, and both may be separated from each other for a quieter device.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. OEC, TI are trademarks of Texas Instruments.

DGV, DV	I, OF	R PV	N P/	ACKAGE
	(TOF	P VI	EW)	)
AI [ AO1 ]	1 2	Ο	24 23	GNDT
GNDT	3		22	BO1
AO2 [	4		21	] GNDG
Vcc			20	V <sub>REF</sub>
AO3	6		19	] GNDG
GNDT [			18	] ERC
AO4 [	8		17	BO2
v <sub>cc</sub> [	9		16	] GNDG
AO5 🛛	10		15	] ві
GNDT [	11		14	OEBA
AO6	12		13	] GNDT

SCES285E-OCTOBER 1999-REVISED APRIL 2005

### **DESCRIPTION/ORDERING INFORMATION (CONTINUED)**

This device is fully specified for hot-insertion applications using  $I_{off}$  and power-up 3-state. The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

This device features adjustable edge-rate control (ERC). Changing the ERC input voltage between GND and  $V_{CC}$  adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load. ERC automatically is selected to the same speed as alternate source 1-to-6 fanout drivers that use pin 18 for 3.3-V or 5-V  $V_{CC}$ .

When  $V_{CC}$  is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable ( $\overline{OE}$ ) input should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

T <sub>A</sub>	PACK	AGE <sup>(1)</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	SOIC – DW	Tube SN74GTLP817DW		GTLP817	
–40°C to 85°C		Tape and reel	SN74GTLP817DWR	GILFOIT	
-40 C 10 65 C	TSSOP – PW	Tape and reel	SN74GTLP817PWR	GT817	
	TVSOP – DGV	Tape and reel	SN74GTLP817DGVR	GT817	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

## FUNCTIONAL DESCRIPTION

The SN74GTLP817 is a fanout driver providing LVTTL-to-GTLP translation and GTLP-to-LVTTL translation in the same package.

The LVTTL-to-GTLP direction is a 1-to-2 fanout driver with a single output enable (OEAB).

The GTLP-to-LVTTL direction is a 1-to-6 fanout driver with a single output enable (OEBA).

Data polarity is inverting for both directions.

### **FUNCTION TABLES**

#### OUTPUT CONTROL (A TO B)

MODE	OUTPUT	PUTS	INF
MODE	BOn	OEAB	AI
Isolation	Z	Н	Х
lassanta el transmenent	L	L	Н
Isolation Inverted transparent	н	L	L

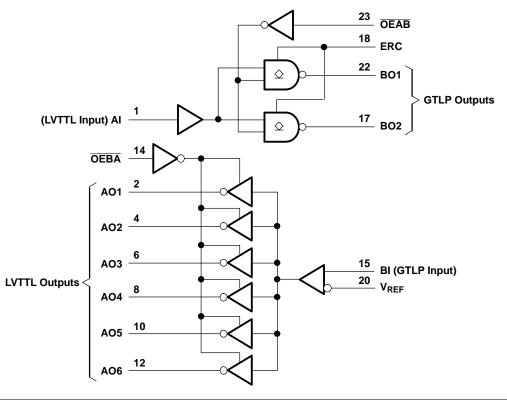
#### OUTPUT CONTROL (B TO A)

INF	PUTS	OUTPUT	MODE
BI	OEBA	AOn	MODE
Х	Н	Z	Isolation
Н	L	L	Inverted transport
L	L	Н	Inverted transparent

#### **B-PORT EDGE-RATE CONTROL (ERC)**

INI	PUT ERC	OUTPUT
LOGIC LEVEL	NOMINAL VOLTAGE	B-PORT EDGE RATE
Н	V <sub>CC</sub>	Slow
L	GND	Fast

### LOGIC DIAGRAM (POSITIVE LOGIC)



SCES285E-OCTOBER 1999-REVISED APRIL 2005

## Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	4.6	V
V <sub>GNDG</sub> – V <sub>GNDT</sub>	Ground dc voltage difference			0.3	V
N/		AI port and control inputs	-0.5	7	V
VI	Input voltage range <sup>(2)</sup>	BI port and V <sub>REF</sub>	-0.5	4.6	v
M	Voltage range applied to any output in the	AO port	-0.5	7	V
Vo	high-impedance or power-off state <sup>(2)</sup>	BO port	-0.5	4.6	v
1	Current into any output in the low state	AO port		24	
Current into any output in the low state	BO port		100	mA	
lo	Current into any A output in the high state <sup>(3)</sup>			24	mA
	Continuous current through each $V_{CC}$ or GNI	0		±100	mA
I <sub>IK</sub>	Input clamp current	V <sub>1</sub> < 0		-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
		DGV package		86	
$\theta_{JA}$	Package thermal impedance <sup>(4)</sup>	DW package		46	°C/W
		PW package		88	
T <sub>stg</sub>	Storage temperature range		-65	150	°C

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings (1) only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed. This current flows only when the output is in the high state and  $V_O > V_{CC}$ . The package thermal impedance is calculated in accordance with JESD 51-7. (2)

(3)

(4)

SCES285E-OCTOBER 1999-REVISED APRIL 2005

# Recommended Operating Conditions<sup>(1)(2)(3)(4)</sup>

			MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		3.15	3.3	3.45	V
V	Termination voltage	GTL	1.14	1.2	1.26	V
V <sub>TT</sub>	Termination voltage	GTLP	1.35	1.5	1.65	v
V		GTL	0.74	0.8	0.87	V
V <sub>REF</sub>	Reference voltage	GTLP	0.87	1	1.1	v
V		BI			V <sub>TT</sub>	V
VI	Input voltage	AI, OE		V <sub>CC</sub>	5.5	v
		BI	V <sub>REF</sub> + 0.05			
V <sub>IH</sub>	/IH High-level input voltage	ERC	V <sub>CC</sub> – 0.6	V <sub>CC</sub>	5.5	V
		AI, OE	2			
		BI			V <sub>REF</sub> – 0.05	
VIL	Low-level input voltage	ERC		GND	0.6	V
		AI, OE			0.8	
I <sub>IK</sub>	Input clamp current				-18	mA
I <sub>OH</sub>	High-level output current	AO port			-12	mA
-		AO port			12	A
I <sub>OL</sub>	Low-level output current	BO port			50	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled			10	ns/V
$\Delta t / \Delta V_{CC}$	Power-up ramp rate		20			μs/V
T <sub>A</sub>	Operating free-air temperature		-40		85	°C

All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.
 Normal connection sequence is GND first and V<sub>CC</sub> = 3.3 V, I/O, control inputs, V<sub>TT</sub>, V<sub>REF</sub> (any order) last.
 V<sub>TT</sub> and R<sub>TT</sub> can be adjusted to accommodate backplane impedances if the dc recommended I<sub>OL</sub> ratings are not exceeded.
 V<sub>REF</sub> can be adjusted to optimize noise margins, but normally is two-thirds V<sub>TT</sub>.

SCES285E-OCTOBER 1999-REVISED APRIL 2005

### **Texas STRUMENTS** www.ti.com

### **Electrical Characteristics**

over recommended operating free-air temperature range for GTLP (unless otherwise noted)

Р	ARAMETER	TEST CONDITION	IS	MIN TY	'P <sup>(1)</sup> MAX	UNIT	
V <sub>IK</sub>		V <sub>CC</sub> = 3.15 V,	I <sub>I</sub> = -18 mA		-1.2	V	
		V <sub>CC</sub> = 3.15 V to 3.45 V,	I <sub>OH</sub> = −100 μA	V <sub>CC</sub> – 0.2			
V	AQ port		I <sub>OH</sub> = −100 μA	V <sub>CC</sub> – 0.2		V	
V <sub>OH</sub>	AO port	V <sub>CC</sub> = 3.15 V	I <sub>OH</sub> =6 mA	2.4		v	
			I <sub>OH</sub> = -12 mA	2.2			
	$V_{CC} = 3.15 \text{ V} \text{ to } 3.45 \text{ V},$	I <sub>OL</sub> = 100 μA		0.2			
			I <sub>OL</sub> = 100 μA		0.2		
	AO port	V <sub>CC</sub> = 3.15 V	$I_{OL} = 6 \text{ mA}$		0.4		
V <sub>OL</sub>	V <sub>OL</sub>		I <sub>OL</sub> = 12 mA		0.5	V	
		V <sub>CC</sub> = 3.15 V	I <sub>OL</sub> = 100 μA		0.2		
	BO port		I <sub>OL</sub> = 40 mA		0.5		
		I <sub>OL</sub> = 50 mA		0.55			
I <sub>I</sub>	BI, AI, OE, ERC	V <sub>CC</sub> = 3.45 V,	V <sub>I</sub> = 0 or 5.5 V		±5	μΑ	
	AO port	V <sub>CC</sub> = 3.45 V	$V_{O} = V_{CC}$		10	^	
I <sub>OZH</sub>	BO port		V <sub>O</sub> = 1.5 V		5	μA	
	AO port	N 0.45 M	V <sub>O</sub> = GND		-10		
I <sub>OZL</sub>	BO port	$V_{CC} = 3.45 V$	V <sub>O</sub> = 5.5 V		-5	μA	
		$V_{CC} = 3.45 \text{ V}, I_{O} = 0,$	Outputs high		10		
I <sub>CC</sub>	AO or BO port	$V_{I}$ (AI or control input) = $V_{CC}$ or GND,	Outputs low		10	mA	
		$V_{I}$ (BI input) = $V_{TT}$ or GND	Outputs disabled		10		
$\Delta I_{CC}^{(2)}$	AI, OE	$V_{CC}$ = 3.45 V, One A-port or control input at $V_{CC}$ – 0.6 V, Other A-port or control inputs at $V_{CC}$ or GND			1	mA	
<u>^</u>	AI, OE, ERC	$V_{I} = V_{CC} \text{ or } 0$			4 4.4	~ Г	
Ci	BI	$V_{I} = V_{TT}$ or 0			3.5 3.9	pF	
<u> </u>	AO port	$V_{O} = V_{CC} \text{ or } 0$			4 4.5	~ Г	
Co	BO port	$V_0 = V_{TT}$ or 0			5 5.4	pF	

(1) All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ . (2) This is the increase in supply current for each input that is at the specified LVTTL voltage level, rather than  $V_{CC}$  or GND.

### **Hot-Insertion Specifications for A Port**

over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS			MAX	UNIT
l <sub>off</sub>	$V_{CC} = 0,$	$V_1$ or $V_0 = 0$ to 5.5 V			10	μΑ
I <sub>OZPU</sub>	$V_{CC} = 0$ to 1.5 V,	$V_{O} = 0.5 V$ to 3 V,	$\overline{OE} = 0$		±30	μΑ
I <sub>OZPD</sub>	$V_{CC} = 1.5 V \text{ to } 0,$	$V_{O}$ = 0.5 V to 3 V,	$\overline{OE} = 0$		±30	μΑ

### **Hot-Insertion Specifications for B Port**

over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS			MAX	UNIT
I <sub>off</sub>	$V_{CC} = 0,$	$V_{I}$ or $V_{O} = 0$ to 1.5 V			10	μA
I <sub>OZPU</sub>	$V_{CC} = 0$ to 1.5 V,	$V_{O} = 0.5 V$ to 1.5 V,	$\overline{OE} = 0$		±30	μA
I <sub>OZPD</sub>	$V_{\rm CC} = 1.5 \ V \ {\rm to} \ 0,$	$V_{O} = 0.5 V$ to 1.5 V,	$\overline{OE} = 0$		±30	μA

### **Switching Characteristics**

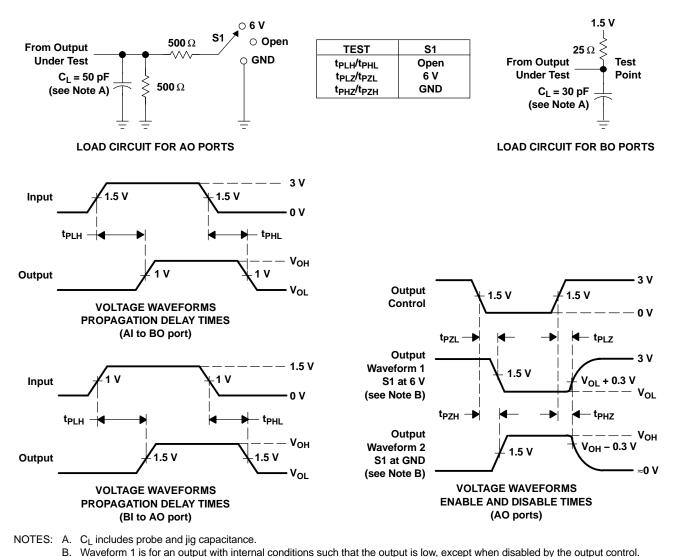
over recommended ranges of supply voltage and operating free-air temperature,  $V_{TT} = 1.5$  V and  $V_{REF} = 1$  V for GTLP (see Figure 1)

INET						
PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE <sup>(1)</sup>	MIN TYP <sup>(2</sup>	) MAX	UNIT
t <sub>PLH</sub>	AI	во	Slow	3	6	ns
t <sub>PHL</sub>	Ai	во	310W	1.8	4.7	115
t <sub>PLH</sub>	AI	во	Fast	2	5	ns
t <sub>PHL</sub>		во	Fasi	1.5	4.2	115
t <sub>en</sub>	OEAB	PO	Slow	3	6.1	ns
t <sub>dis</sub>		BO	Slow	2	4.7	
t <sub>en</sub>	OEAB	BO Fas	Feet	2.1	6	
t <sub>dis</sub>			Fasi	1.5	4.7	ns
	Dias time. Desute	ute (200/ te 200/)	Slow	2.	5	
t <sub>r</sub>	Rise lime, b oulp	uts (20% to 80%)	Fast	1.4		ns
	Fall time Davita	the (0,00% the 0,00%)	Slow	1.	7	
t <sub>f</sub>	Fail line, b oulp	uts (80% to 20%)	Fast		1	ns
t <sub>PLH</sub>	BI	AO		2.3	6	20
t <sub>PHL</sub>	DI			1.9	4.7	ns
t <sub>en</sub>	OEBA	40		1.1	6.3	
t <sub>dis</sub>	UEBA	AO		1.2	5	ns

(1)

Slow (ERC = V<sub>CC</sub>) and Fast (ERC = GND) All typical values are at V<sub>CC</sub> = 3.3 V,  $T_A$  = 25°C. (2)

SCES285E-OCTOBER 1999-REVISED APRIL 2005



PARAMETER MEASUREMENT INFORMATION

7 Texas Istruments

www.ti.com

B. Waveform 1 is for an output with internal condit Waveform 2 is for an autput with internal condit

- Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\approx$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub>  $\approx$  2 ns, t<sub>f</sub>  $\approx$  2 ns.

D. The outputs are measured one at a time, with one transition per measurement.

#### Figure 1. Load Circuits and Voltage Waveforms

#### Distributed-Load Backplane Switching Characteristics

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application probably is a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

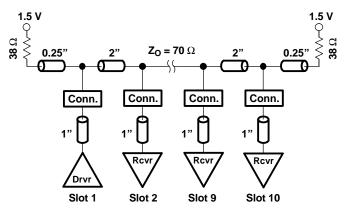


Figure 2. Medium-Drive Test Backplane

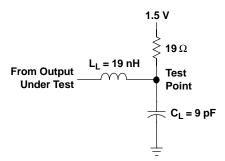


Figure 3. Medium-Drive RLC Network

SCES285E-OCTOBER 1999-REVISED APRIL 2005

# www.ti.com

### **Switching Characteristics**

over recommended ranges of supply voltage and operating free-air temperature,  $V_{\rm TT}$  = 1.5 V and  $V_{\rm REF}$  = 1 V for GTLP (see Figure 3)

PARAMETER	FROM TO (INPUT) (OUTPUT)		EDGE RATE <sup>(1)</sup>	TYP <sup>(2)</sup>	UNIT
t <sub>PLH</sub>	AI	во	Slow	4.4	ns
t <sub>PHL</sub>	AI	во	SIOW	4.4	
t <sub>PLH</sub>	AI	во	Fast	3.2	ns
t <sub>PHL</sub>	AI	во	Fasi	3.2	
t <sub>en</sub>	OEAB	DO	Claur	4	ns
t <sub>dis</sub>	- OEAB	BO	Slow	4.4	
t <sub>en</sub>	OEAB	во	Fast	2.9	ns
t <sub>dis</sub>	UEAD	во	Fasi	3.1	
t <sub>r</sub>	Diag time. D gute	Slow	1.8	B ns	
	Rise time, B outp	Fast	1		
	Fall time Davita	Slow	2		
t <sub>f</sub>	Fall time, B outp	Fast	1.6	ns	

(1) Slow (ERC =  $V_{CC}$ ) and Fast (ERC = GND) (2) All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C. All values are derived from TI-SPICE models.



### PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
SN74GTLP817PW	Active	Production	TSSOP (PW)   24	60   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GT817
SN74GTLP817PW.B	Active	Production	TSSOP (PW)   24	60   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GT817

<sup>(1)</sup> **Status:** For more details on status, see our product life cycle.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## TEXAS INSTRUMENTS

www.ti.com

23-May-2025

## TUBE



## - B - Alignment groove width

\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74GTLP817PW	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74GTLP817PW.B	PW	TSSOP	24	60	530	10.2	3600	3.5

# **PW0024A**



# **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



# PW0024A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# PW0024A

# **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025, Texas Instruments Incorporated